

Steven Chuang

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

13
papers

2,961
citations

13
h-index

13
g-index

13
ext. papers

3,237
ext. citations

12.9
avg, IF

4.7
L-index

#	Paper	IF	Citations
13	High-performance single layered WSe ₂ -FETs with chemically doped contacts. <i>Nano Letters</i> , 2012 , 12, 3788-92	11.5	1322
12	MoSIP-type transistors and diodes enabled by high work function MoO _x contacts. <i>Nano Letters</i> , 2014 , 14, 1337-42	11.5	419
11	Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors. <i>Nature</i> , 2010 , 468, 286-9	50.4	327
10	High-gain inverters based on WSe ₂ complementary field-effect transistors. <i>ACS Nano</i> , 2014 , 8, 4948-53	16.7	249
9	Hole contacts on transition metal dichalcogenides: interface chemistry and band alignments. <i>ACS Nano</i> , 2014 , 8, 6265-72	16.7	149
8	Ballistic InAs nanowire transistors. <i>Nano Letters</i> , 2013 , 13, 555-8	11.5	138
7	Nanoscale InGaSb heterostructure membranes on Si substrates for high hole mobility transistors. <i>Nano Letters</i> , 2012 , 12, 2060-6	11.5	74
6	Ultrathin body InAs tunneling field-effect transistors on Si substrates. <i>Applied Physics Letters</i> , 2011 , 98, 113105	3.4	69
5	Near-ideal electrical properties of InAs/WSe ₂ van der Waals heterojunction diodes. <i>Applied Physics Letters</i> , 2013 , 102, 242101	3.4	64
4	Patterned p-doping of InAs nanowires by gas-phase surface diffusion of Zn. <i>Nano Letters</i> , 2010 , 10, 509-11	13.5	54
3	Direct growth of single-crystalline III-V semiconductors on amorphous substrates. <i>Nature Communications</i> , 2016 , 7, 10502	17.4	37
2	Benchmarking the performance of ultrathin body InAs-on-insulator transistors as a function of body thickness. <i>Applied Physics Letters</i> , 2011 , 99, 103507	3.4	37
1	Ultrathin-Body High-Mobility InAsSb-on-Insulator Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 504-506	4.4	22